2SC1573, 2SC1573A, 2SC1573B

Silicon NPN triple diffusion planar type

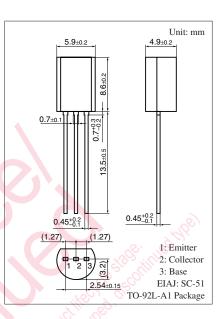
For high breakdown voltage general amplification For small TV video output Complementary to 2SC1573 and 2SA0879

Features

- \bullet High collector-emitter voltage (Base open) $V_{\mbox{\scriptsize CEO}}$
- High transition frequency f_T

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SC1573	V _{CBO}	250	V
(Emitter open)	2SC1573A		300	
	2SC1573B		400	
Collector-emitter voltage	2SC1573	V _{CEO}	200	V
(Base open)	2SC1573A		300	
	2SC1573B		400	
Emitter-base voltage	2SC1573	V _{EBO}	5	V
(Collector open)	2SC1573A		7	
	2SC1573B			
Collector current		I _C	70	mA
Peak collector current		I _{CP}	100	mA
Collector power dissipation		P _C	1	W
Junction temperature		Tj	150	C C
Storage temperature		T _{stg}	-55 to +150	°C

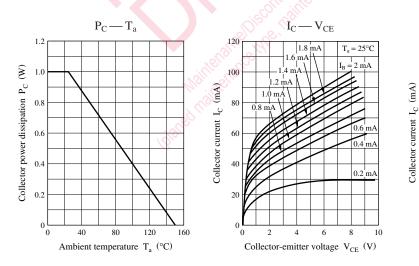


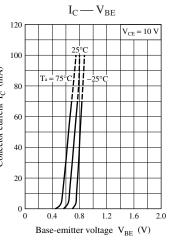
Electrical Characteristics	$T_a = 25^{\circ}C \pm 3^{\circ}C$
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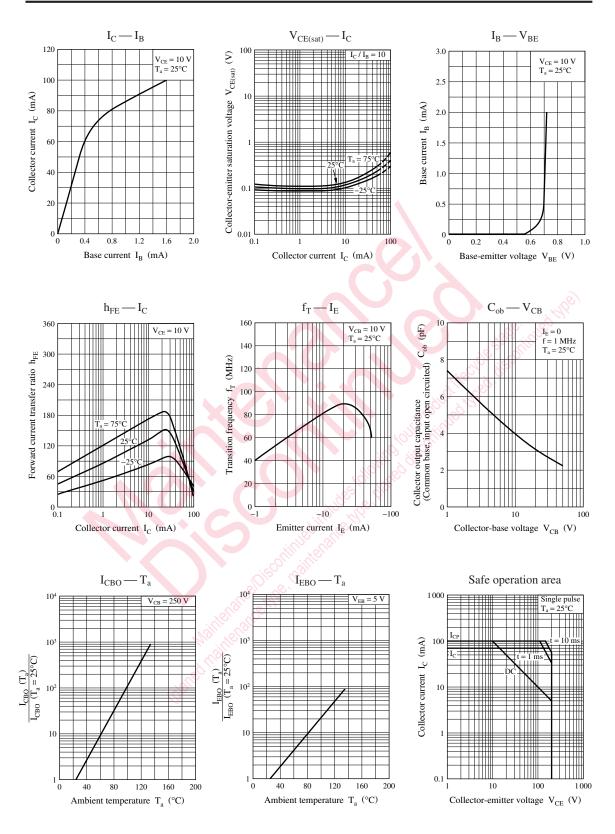
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SC1573	V _{CEO}	$I_{C} = 100 \ \mu A, I_{B} = 0$	200			V
(Base open)	2SC1573A	1		300			
	2SC1573B	1		400			
Emitter-base voltage	2SC1573	V _{EBO}	$I_E = 1 \ \mu A, I_C = 0$	5			V
(Collector open)	2SC1573A	1		7			
	2SC1573B]		7			
Collector-base cut-off current	2SC1573	I _{CBO}	$V_{CB} = 12 \text{ V}, I_E = 0$			2	μΑ
(Emitter open)	2SC1573A						
	2SC1573B]	$V_{CB} = 200 \text{ V}, I_E = 0$			10	
Forward current transfer ratio	2SC1573	h _{FE} *	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	60		220	—
	2SC1573A			30		220	
	2SC1573B	1					
Collector-emitter saturation	voltage	V _{CE(sat)}	$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5 \text{ mA}$			1.2	V.
Transition frequency		f _T	$V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 200 \text{ MHz}$	50	80		MHz
Collector output capacitance	2SC1573	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		5	\$ 10 \$	pF
(Common base, input	2SC1573A				4	8]
open circuited)	2SC1573B	1		Ś	\$ 4%	8	1

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Rank classification (2SC1573 for ranks Q and R only)

Rank	Р	Q	R
h _{FE}	30 to 100	60 to 150	100 to 220







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